

# Atsushi Ogura

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Modification and Characterization of Interfacial Bonding for Thermal Management of Ruthenium Interconnects in Next-Generation Very-Large-Scale Integration Circuits. ACS Applied Materials & Interfaces, 2022, 14, 7392-7404.	8.0	8
2	Operando hard X-ray photoelectron spectroscopy study of buried interface chemistry of Au/InO <sub>1.16</sub> Co <sub>0.04</sub> /Al <sub>2</sub> O <sub>3</sub> /p<math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e383" altimg="si20.svg"><mml:msup><mml:mrow /><mml:mrow><mml:mo>+</mml:mo></mml:mrow></mml:msup></mml:math>-Si stacks. Applied Surface Science, 2022, 593, 153272.	6.1	1
3	Detection Limit of Photoluminescence Method for Determination of Carbon Impurity Concentration in Silicon. , 2022, , .		0
4	Oxygen Precipitation Behavior in n-Type Cz-Si Related to Carbon Concentration and Crystal Growth Conditions. Journal of Electronic Materials, 2021, 50, 1474-1481.	2.2	0
5	Free-to-bound emission from interstitial carbon and oxygen defects (C<sub>i</sub>O<sub>i</sub>) in electron-irradiated Si. Applied Physics Express, 2021, 14, 011006.	2.4	0
6	Comparison of characteristics of thin-film transistor with In<sub>2</sub>O<sub>3</sub> and carbon-doped In<sub>2</sub>O<sub>3</sub> channels by atomic layer deposition and post-metallization annealing in O<sub>3</sub>. Japanese Journal of Applied Physics, 2021, 60, 030903.	1.5	6
7	Thermal conductivity and inelastic X-ray scattering measurements on SiGeSn polycrystalline alloy. Japanese Journal of Applied Physics, 2021, 60, S88F11.	1.5	5
8	Simulation study on lateral minority carrier transport in the surface inversion layer of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. Japanese Journal of Applied Physics, 2021, 60, 026503.	1.5	2
9	Correlation between ferroelectricity and ferroelectric orthorhombic phase of HfxZr1-xO2 thin films using synchrotron x-ray analysis. APL Materials, 2021, 9, .	5.1	9
10	Influence of adsorbed oxygen concentration on characteristics of carbon-doped indium oxide thin-film transistors under bias stress. Japanese Journal of Applied Physics, 2021, 60, SCCM01.	1.5	3
11	Effects of Zn<sub>x</sub>Mn<sub>1-x</sub>S buffer layer on nonpolar AlN growth on Si (100) substrate. Japanese Journal of Applied Physics, 2021, 60, SCCG02.	1.5	0
12	Evaluation of $\text{MoS}_{2(1-x)}\text{Te}_{2x}$ fabricated by different bottom-up methods. , 2021, , .		0
13	Phonon properties of group IV materials for thermoelectric applications. , 2021, , .		0
14	Investigation of the Chemical Reaction between Silver Electrodes and Transparent Conductive Oxide Films for the Improvement of Fill Factor of Silicon Heterojunction Solar Cells. ECS Journal of Solid State Science and Technology, 2021, 10, 055013.	1.8	4
15	Dependency of a localized phonon mode intensity on compositional cluster size in SiGe alloys. AIP Advances, 2021, 11, 075017.	1.3	3
16	Evaluation of correlation between fill factor and high mobility transparent conductive oxide film deposition temperature in the silicon heterojunction solar cells. Materials Science in Semiconductor Processing, 2021, 132, 105887.	4.0	6
17	Synthesis, characterization and application of intracellular Ag/AgCl nanohybrids biosynthesized in Scenedesmus sp. as neutral lipid inducer and antibacterial agent. Environmental Research, 2021, 201, 111499.	7.5	15
18	Atomic mass dependency of a localized phonon mode in SiGe alloys. AIP Advances, 2021, 11, .	1.3	8

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19	Strain evaluation in Ge and Sn implanted Si layers with laser and rapid thermal annealing. Materials Science in Semiconductor Processing, 2020, 120, 105282.	4.0	2
20	Temperature and polarity dependence of electrical properties of ZnO film on pyroelectric LiNbO <sub>3</sub> single crystal. Japanese Journal of Applied Physics, 2020, 59, SIIG11.	1.5	0
21	Phonon dispersion of bulk Ge-rich SiGe: inelastic X-ray scattering studies. Japanese Journal of Applied Physics, 2020, 59, 061003.	1.5	4
22	Synthesis of $\text{MoS}_2(1-x)\text{Te}_2x$ by Sputtering and the Change in the Physical Properties and Structure Depending on the Chalcogen Composition. , 2020, , .		0
23	Improvement in ferroelectricity and breakdown voltage of over 20-nm-thick Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> bilayer by atomic layer deposition. Applied Physics Letters, 2020, 117, .	3.3	17
24	Evaluation of MoS <sub>2</sub> Films Fabricated by Metal-Organic Chemical Vapor Deposition Using a Novel Mo Precursor i-Pr <sub>2</sub> DADMo(CO) <sub>3</sub> Under Various Deposition Conditions. MRS Advances, 2020, 5, 1643-1652.	0.9	0
25	Thermal conductivity characteristics in polycrystalline silicon with different average sizes of grain and nanostructures in the grains by UV Raman spectroscopy. Japanese Journal of Applied Physics, 2020, 59, 075501.	1.5	4
26	Quantification of Ge fraction using local vibrational modes in Raman spectra of silicon germanium by oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2020, 59, 075502.	1.5	0
27	Enlargement of grain size for MoS <sub>2</sub> film fabricated by RF magnetron sputtering with additional DC bias by optimization of deposition parameters and its evaluation with Raman spectroscopy. Japanese Journal of Applied Physics, 2020, 59, 065502.	1.5	1
28	Anomalous low energy phonon dispersion in bulk silicon-germanium observed by inelastic x-ray scattering. Applied Physics Letters, 2020, 116, .	3.3	10
29	The Physical and Chemical Properties of MoS <sub>2</sub> (1-x)Te <sub>2x</sub> Alloy Synthesized by Co-sputtering and Chalcogenization and Their Dependence on Fabrication Conditions. MRS Advances, 2020, 5, 1635-1642.	0.9	4
30	Stress evaluation induced by wiggling silicon nitride fine pattern using Raman spectroscopy. Japanese Journal of Applied Physics, 2020, 59, SIIF03.	1.5	1
31	Band alignment at non-polar AlN/MnS interface investigated by hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2020, 59, SIIG07.	1.5	2
32	Anisotropic biaxial stress evaluation in metal-organic chemical vapor deposition grown Ge <sub>1</sub> -Sn mesa structure by oil-immersion Raman spectroscopy. Thin Solid Films, 2020, 697, 137797.	1.8	2
33	Improvement of Ferroelectricity and Fatigue Property of Thicker Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> Bi-layer. ECS Transactions, 2020, 98, 63-70.	0.5	9
34	Observation of an Unidentified Phonon Peak in SiGe Alloys and Superlattices Using Molecular Dynamics Simulation. ECS Transactions, 2020, 98, 533-546.	0.5	5
35	Surface inversion layer effective minority carrier mobility as one of the measures of surface quality of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. Japanese Journal of Applied Physics, 2020, 59, SGGF06.	1.5	1
36	Evaluation of plasma induced defects on silicon substrate by solar cell fabrication process. Japanese Journal of Applied Physics, 2020, 59, 071003.	1.5	7

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37	Anomalous excitation-power dependence of band-edge emission in Si involving radiation-induced defects. Japanese Journal of Applied Physics, 2020, 59, 106502.	1.5	4
38	Detection limit of carbon concentration measurement in Si for photoluminescence method after electron irradiation. Japanese Journal of Applied Physics, 2020, 59, 126501.	1.5	3
39	Normally-off sputtered-MoS <sub>2</sub> nMISFETs with TiN top-gate electrode all defined by optical lithography for chip-level integration. Japanese Journal of Applied Physics, 2020, 59, 080906.	1.5	6
40	The Electronic and Physical Structure Evaluation of MoS <sub>2</sub> (1-x)Te <sub>2x</sub> Alloy Fabricated with Co-Sputtering and Post-Deposition Annealing in Chalcogen Ambient. ECS Journal of Solid State Science and Technology, 2020, 9, 093018.	1.8	1
41	Origin of carrier lifetime degradation in floating-zone silicon during a high-temperature process for insulated gate bipolar transistor. Japanese Journal of Applied Physics, 2020, 59, 115503.	1.5	0
42	Evaluation of thermal conductivity characteristics in Si nanowire covered with oxide by UV Raman spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SDDF04.	1.5	1
43	Effects of substrate self-bias and nitrogen flow rate on non-polar AlN film growth by reactive sputtering. Japanese Journal of Applied Physics, 2019, 58, SDDG07.	1.5	8
44	3300V Scaled IGBTs Driven by 5V Gate Voltage. , 2019, , .		6
45	Effects of surface recombination and excitation power on quantitative analysis of carbon in Si using room-temperature photoluminescence after electron irradiation. Japanese Journal of Applied Physics, 2019, 58, 076502.	1.5	4
46	Improvement in ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using top- and bottom-ZrO <sub>2</sub> nucleation layers. APL Materials, 2019, 7, .	5.1	46
47	Evaluation of Sn-Doped Indium Oxide Film and Interface Properties on a-Si Formed by Reactive Plasma Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, Q101-Q105.	1.8	7
48	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. Solar Energy, 2019, 188, 1292-1297.	6.1	10
49	Normally-Off Sputtered-MoS <sub>2</sub> nMISFETs with MoSi <sub>2</sub> Contact by Sulfur Powder Annealing and ALD Al <sub>2</sub> O <sub>3</sub> Gate Dielectric for Chip Level Integration. , 2019, , .		3
50	Ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films fabricated by 300°C low temperature process with plasma-enhanced atomic layer deposition. Microelectronic Engineering, 2019, 215, 111013.	2.4	55
51	Lifetime Degradation by Oxygen Precipitation Combined with Metal Contamination in Czochralski Silicon for Solar Cells. ECS Journal of Solid State Science and Technology, 2019, 8, Q72-Q75.	1.8	5
52	Crystal growth of a MnS buffer layer for non-polar AlN on Si (100) deposited by radio frequency magnetron sputtering. Japanese Journal of Applied Physics, 2019, 58, SBBK03.	1.5	3
53	Evaluations of minority carrier lifetime in floating zone Si affected by Si insulated gate bipolar transistor processes. Japanese Journal of Applied Physics, 2019, 58, SBBD07.	1.5	1
54	Effect of oxygen precipitation through annealing process on lifetime degradation by Czochralski-Si crystal growth conditions. Japanese Journal of Applied Physics, 2019, 58, SBBF02.	1.5	6

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55	Anisotropic Biaxial Strain Evaluation in Carbon-Doped Silicon Using Water-Immersion Raman Spectroscopy. ECS Transactions, 2019, 92, 33-39.	0.5	2
56	Switching of 3300V Scaled IGBT by 5V Gate Drive. , 2019, , .		0
57	Effect of post-deposition annealing on electrical properties and structures of aluminum oxide passivation film on a crystalline silicon substrate. Japanese Journal of Applied Physics, 2019, 58, 125502.	1.5	1
58	Effects of damages induced by indium-tin-oxide reactive plasma deposition on minority carrier lifetime in silicon crystal. AIP Advances, 2019, 9, .	1.3	8
59	Characteristics of Oxide TFT Using Carbon-Doped $\text{In}^{TM}_{n2}$ $\text{O}_3$ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium ( $\text{In}^{TM}_{n}\text{-EtCp}$ ) and $\text{H}_2\text{O}$ & $\text{O}_3$ . ECS Transactions, 2019, 92, 3-13.	0.5	17
60	Investigation of Novel Te precursor ( $\text{i-C}_3\text{H}_7$ ) $_2\text{Te}$ for $\text{MoTe}_2$ Fabrication. MRS Advances, 2018, 3, 321-326.	0.9	1
61	MOCVD of Monolayer $\text{MoS}_2$ using Novel Molybdenum Precursor $\text{i-Pr}_2\text{DADMo}(\text{CO})_3$ . MRS Advances, 2018, 3, 379-384.	0.9	10
62	Low-Carrier-Density Sputtered $\text{MoS}_2$ Film by Vapor-Phase Sulfurization. Journal of Electronic Materials, 2018, 47, 3497-3501.	2.2	36
63	Improved leakage current properties of $\text{ZrO}_2/(\text{Ta}/\text{Nb})\text{O}_x/\text{Al}_2\text{O}_3/\text{ZrO}_2$ nanolaminate insulating stacks for dynamic random access memory capacitors. Thin Solid Films, 2018, 655, 48-53.	1.8	16
64	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. ACS Applied Nano Materials, 2018, 1, 915-921.	5.0	11
65	Origin of room-temperature photoluminescence around C-line in electron-irradiated Si and its applicability for quantification of carbon. Applied Physics Express, 2018, 11, 041301.	2.4	9
66	Study of Sn and Mg doping effects on $\text{TiO}_2/\text{Ge}$ stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2018, 57, 04FJ04.	1.5	0
67	Distribution of light-element impurities in Si crystals grown by seed-casting method. Japanese Journal of Applied Physics, 2018, 57, 08RB19.	1.5	1
68	Determination of C concentration in P-doped n-type Czochralski-grown Si crystals by liquid N temperature photoluminescence after electron irradiation. Japanese Journal of Applied Physics, 2018, 57, 08RB06.	1.5	5
69	Demonstration of 1200V Scaled IGBTs Driven by 5V Gate Voltage with Superiorly Low Switching Loss. , 2018, , .		21
70	Evaluation of Anisotropic Three-Dimensional Strain Relaxation in Stripe-Shaped $\text{Ge}_{1-x}\text{Sn}_x$ Mesa Structure. ECS Transactions, 2018, 86, 329-336.	0.5	3
71	Reliability of $\text{Al}_2\text{O}_3/\text{In-Si-O-C}$ Thin-Film Transistors with an $\text{Al}_2\text{O}_3$ Passivation Layer under Gate-Bias Stress. ECS Transactions, 2018, 86, 135-145.	0.5	4
72	Ferroelectricity of $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$ Thin Films Fabricated Using TiN Stressor and $\text{ZrO}_2$ Nucleation Techniques. ECS Transactions, 2018, 86, 31-38.	0.5	9

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73	Determination of Phonon Deformation Potentials in Carbon-Doped Silicon. ECS Transactions, 2018, 86, 419-425.	0.5	2
74	Study on chemical bonding states at electrode-silicon interface fabricated with fire-through control paste. Japanese Journal of Applied Physics, 2018, 57, 08RB23.	1.5	1
75	Sputter-Deposited-MoS <sub>2</sub> MISFETs With Top-Gate and Al <sub>2</sub> O <sub>3</sub> Passivation Under Low Thermal Budget for Large Area Integration. IEEE Journal of the Electron Devices Society, 2018, 6, 1246-1252.	2.1	10
76	(Invited) High-Sn Concentration MOCVD-Grown Strained GeSn Thin Films Evaluated Using HAXPES and XRD Base on Synchrotron Technique. ECS Transactions, 2018, 86, 411-418.	0.5	1
77	Evaluation of Laterally Graded Silicon Germanium Wires for Thermoelectric Devices Fabricated by Rapid Melting Growth. ECS Transactions, 2018, 86, 87-93.	0.5	8
78	Strain Evaluation of Laser-Annealed SiGe Thin Layers. ECS Transactions, 2018, 86, 59-65.	0.5	2
79	Investigation on Mo <sub>1-x</sub> W <sub>x</sub> S <sub>2</sub> fabricated by co-sputtering and post-deposition sulfurization with C <sub>4</sub> H <sub>9</sub> S <sub>2</sub> . Japanese Journal of Applied Physics, 2018, 57, 06HB04.	1.5	2
80	Determination of phonon deformation potentials and strain-shift coefficients in Ge-rich Si <sub>1-x</sub> Ge <sub>x</sub> using bulk Ge-rich Si <sub>1-x</sub> Ge <sub>x</sub> crystals and oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 106601.	1.5	12
81	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 061206.	1.2	5
82	Evaluation of oxygen precipitation behavior in n-type Czochralski-Si for photovoltaic by infrared tomography: Effects of carbon concentration and annealing process conditions. Japanese Journal of Applied Physics, 2018, 57, 08RB01.	1.5	1
83	Potential of chemical rounding for the performance enhancement of pyramid textured p-type emitters and bifacial n-PERT Si cells. Current Applied Physics, 2018, 18, 1268-1274.	2.4	6
84	Control of dipole properties in high-k and SiO <sub>2</sub> stacks on Si substrates with tricolor superstructure. Applied Physics Letters, 2018, 113, .	3.3	10
85	Suppression of Sulfur Desorption of High-Temperature Sputtered MoS <sub>2</sub> Film by Applying DC Bias. ECS Transactions, 2018, 85, 531-539.	0.5	5
86	Evaluation of Anisotropic Biaxial Stress Induced Around Trench Gate of Si Power Transistor Using Water-Immersion Raman Spectroscopy. Journal of Electronic Materials, 2018, 47, 5050-5055.	2.2	2
87	Determination of Low C Concentration in Czochralski-Grown Si for Solar Cell Applications by Liquid-N-Temperature Photoluminescence After Electron Irradiation. Journal of Electronic Materials, 2018, 47, 5056-5060.	2.2	3
88	Evaluation of saw damage using diamond-coated wire in crystalline silicon solar cells by photoluminescence imaging. Japanese Journal of Applied Physics, 2018, 57, 055702.	1.5	5
89	Miniaturized planar Si-nanowire micro-thermoelectric generator using exuded thermal field for power generation. Science and Technology of Advanced Materials, 2018, 19, 443-453.	6.1	43
90	Effects of particle size of aluminum powder in silver/aluminum paste on n-type solar cells. AIMS Materials Science, 2018, 5, 614-623.	1.4	3

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91	Role of H <sub>2</sub> supply for Sn incorporations in MOCVD Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial growth. Journal of Crystal Growth, 2017, 468, 605-609.	1.5	6
92	Effects of thermal budget in n-type bifacial solar cell fabrication processes on effective lifetime of crystalline silicon. AIP Advances, 2017, 7, .	1.3	12
93	Quantitative relationship between sputter-deposited-MoS <sub>2</sub> properties and underlying-SiO <sub>2</sub> surface roughness. Applied Physics Express, 2017, 10, 041202.	2.4	26
94	Investigation of the static electric field effect of strontium silicate layers on silicon substrates. Journal of Applied Physics, 2017, 121, 225302.	2.5	3
95	Investigation on MoS <sub>2</sub> (1-x)Te <sub>2x</sub> Mixture Alloy Fabricated by Co-sputtering Deposition. MRS Advances, 2017, 2, 1557-1562.	0.9	3
96	Local anisotropic strain evaluation in thin Ge epitaxial film using SiGe stressor template grown on Ge substrate by selective ion implantation. Japanese Journal of Applied Physics, 2017, 56, 110313.	1.5	7
97	Enhanced nickelidation rate in silicon nanowires with interfacial lattice disorder. Journal of Applied Physics, 2017, 122, .	2.5	6
98	The electrical losses induced by silver paste in n-type silicon solar cells. Japanese Journal of Applied Physics, 2017, 56, 102302.	1.5	3
99	Quantification of C in Si by photoluminescence at liquid N temperature after electron irradiation. Applied Physics Express, 2017, 10, 046602.	2.4	12
100	Improvement in ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using ZrO <sub>2</sub> seed layer. Applied Physics Express, 2017, 10, 081501.	2.4	63
101	Characterization of Glass Frit in Conductive Paste for N-Type Crystalline Silicon Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 1313-1318.	2.5	7
102	Band gap-tuned MoS <sub>2</sub> (1-x)Te <sub>2x</sub> thin films synthesized by a hybrid Co-sputtering and post-deposition tellurization annealing process. Journal of Materials Research, 2017, 32, 3021-3028.	2.6	6
103	Improvement of smooth surface of RuO <sub>2</sub> bottom electrode on Al <sub>2</sub> O <sub>3</sub> buffer layer and characteristics of RuO <sub>2</sub> /TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> /RuO <sub>2</sub> capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	8
104	Probing spatial heterogeneity in silicon thin films by Raman spectroscopy. Scientific Reports, 2017, 7, 16549.	3.3	3
105	Determination of low carbon concentration in Czochralski-grown Si crystals for solar cells by luminescence activation using electron irradiation. Japanese Journal of Applied Physics, 2017, 56, 070305.	1.5	9
106	Effects of Reaction Conditions on MoS <sub>2</sub> Thin Film Formation Synthesized by Chemical Vapor Deposition using Organic Precursor. MRS Advances, 2017, 2, 1533-1538.	0.9	4
107	Pattern-dependent anisotropic stress evaluation in SiGe epitaxially grown on a Si substrate with selective Ar <sup>+</sup> ion implantation using oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2017, 56, 051301.	1.5	1
108	Evaluation of controlled strain in silicon nanowire by UV Raman spectroscopy. Japanese Journal of Applied Physics, 2017, 56, 06GG10.	1.5	4



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109	Effect of Y and Mn doping into rutile type TiO <sub>2</sub> /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2017, 56, 06GF11.	1.5	3
110	Properties of single-layer MoS <sub>2</sub> film fabricated by combination of sputtering deposition and post deposition sulfurization annealing using (t-C <sub>4</sub> H <sub>9</sub> ) <sub>2</sub> S <sub>2</sub> . Japanese Journal of Applied Physics, 2016, 55, 06GF01.	1.5	16
111	Investigation of new stacking surface passivation structures with interfacial tuning layers on p-type crystalline silicon. Japanese Journal of Applied Physics, 2016, 55, 04ES03.	1.5	0
112	Thin-film growth of (110) rutile TiO <sub>2</sub> on (100) Ge substrate by pulsed laser deposition. Japanese Journal of Applied Physics, 2016, 55, 06GG06.	1.5	2
113	Improving crystalline quality of sputtering-deposited MoS <sub>2</sub> thin film by postdeposition sulfurization annealing using (t-C <sub>4</sub> H <sub>9</sub> ) <sub>2</sub> S <sub>2</sub> . Japanese Journal of Applied Physics, 2016, 55, 04EJ07.	1.5	26
114	Positive and negative dipole layer formation at high-k/SiO <sub>2</sub> interfaces simulated by classical molecular dynamics. Japanese Journal of Applied Physics, 2016, 55, 04EB03.	1.5	25
115	Minority Carrier Recombination Properties of Crystalline Defect on Silicon Surface Induced by Plasma Enhanced Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2016, 5, Q253-Q256.	1.8	14
116	Correlation between chemical-bonding states and fixed-charge states of Sr-silicate film on Si(100) substrate. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	4
117	Effects of Aluminum in Metallization Paste on the Electrical Losses in Bifacial N-type Crystalline Silicon Solar Cells. Energy Procedia, 2016, 98, 106-114.	1.8	14
118	Detection of short range order in SiO <sub>2</sub> thin-films by grazing-incidence wide and small-angle X-ray scattering. Journal of Applied Physics, 2016, 119, 154103.	2.5	1
119	In-Plane Biaxial Strain Evaluation Induced in Ge <sub>1-x</sub> Sn <sub>x</sub> Films Using Oil-Immersion Raman Spectroscopy. ECS Transactions, 2016, 75, 589-597.	0.5	1
120	A study on the evaluation method of glass frit paste for crystalline silicon solar cells. , 2016, , .		3
121	Crystallinity Evaluation of Low Temperature Polycrystalline Silicon Thin Film Using UV/Visible Raman Spectroscopy. ECS Transactions, 2016, 72, 249-255.	0.5	3
122	Prospectively of Carbon-Doped Indium-Tungsten-Oxide Channel TFT for Bias Stress Instability. ECS Transactions, 2016, 75, 149-156.	0.5	5
123	Origin of additional broad peaks in Raman spectra from thin germanium-rich silicon-germanium films. Applied Physics Express, 2016, 9, 071301.	2.4	7
124	Large Scale Uniformity of Sputtering Deposited Single- and Few-Layer MoS <sub>2</sub> Investigated by XPS Multipoint Measurements and Histogram Analysis of Optical Contrast. ECS Journal of Solid State Science and Technology, 2016, 5, Q3012-Q3015.	1.8	12
125	Biaxial stress evaluation in GeSn film epitaxially grown on Ge substrate by oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 091301.	1.5	18
126	Development of Interatomic Potential of Group IV Alloy Semiconductors for Lattice Dynamics Simulation. ECS Transactions, 2016, 75, 785-794.	0.5	2



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127	Role of High-k Interlayer in ZrO <sub>2</sub> /High-k/ZrO <sub>2</sub> Insulating Multilayer on Electrical Properties for DRAM Capacitor. ECS Transactions, 2016, 75, 667-674.	0.5	12
128	Oxygen precipitates distributed around random grain boundaries in a cast-grown multicrystalline silicon crystal. Japanese Journal of Applied Physics, 2016, 55, 041302.	1.5	4
129	Electrically active light-element complexes in silicon crystals grown by cast method. Japanese Journal of Applied Physics, 2016, 55, 095502.	1.5	1
130	Room temperature formation of Hf-silicate layer by pulsed laser deposition with Hf-Si-O ternary reaction control. AIP Advances, 2016, 6, 105303.	1.3	0
131	Examination of phonon deformation potentials for accurate strain measurements in silicon-germanium alloys with the whole composition range by Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 026602.	1.5	8
132	Evaluation of Sputtering Deposited 2-Dimensional MoS <sub>2</sub> Film by Raman Spectroscopy. Materials Research Society Symposia Proceedings, 2015, 1781, 11-16.	0.1	12
133	Multi-layered MoS <sub>2</sub> film formed by high-temperature sputtering for enhancement-mode nMOSFETs. Japanese Journal of Applied Physics, 2015, 54, 04DN08.	1.5	53
134	Influence of Al <sub>2</sub> O <sub>3</sub> layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	6
135	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2015, 54, 08KD12.	1.5	16
136	Photoluminescence due to impurity-cluster-bound exciton in highly doped and highly compensated Si. Japanese Journal of Applied Physics, 2015, 54, 111304.	1.5	5
137	On the Origin of the Gate Oxide Failure Evaluated by Raman Spectroscopy. ECS Transactions, 2015, 66, 237-243.	0.5	1
138	Photoluminescence characterization of Si crystals for microelectronic and photovoltaic devices. , 2015, , .		0
139	Structural Analyses of Thin SiO <sub>2</sub> Films Formed by Thermal Oxidation of Atomically Flat Si Surface by Using Synchrotron Radiation X-Ray Characterization. ECS Journal of Solid State Science and Technology, 2015, 4, N96-N98.	1.8	5
140	Evaluation of Anisotropic Biaxial Stress in Si <sub>1-x</sub> Ge <sub>x</sub> /Ge Mesa-Structure by Oil-Immersion Raman Spectroscopy. ECS Transactions, 2015, 66, 39-45.	0.5	11
141	Advantage in solar cell efficiency of high-quality seed cast mono Si ingot. Applied Physics Express, 2015, 8, 062301.	2.4	17
142	Relationship between passivation properties and band alignment in O <sub>3</sub> -based atomic-layer-deposited AlOx crystalline Si for photovoltaic applications. Japanese Journal of Applied Physics, 2015, 54, 08KD19.	1.5	6
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